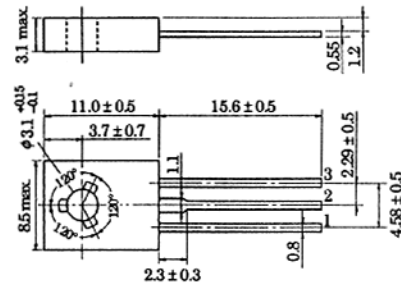


2SB874

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER
COMPLEMENTARY PAIR WITH 2SD1177



1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

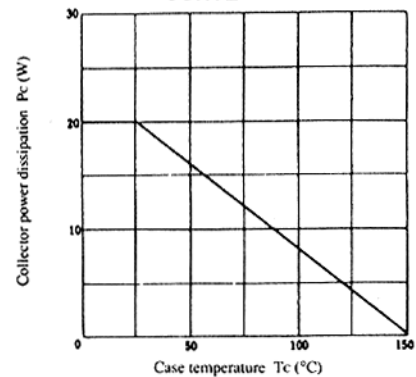
(JEDEC TO-18 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB874	Unit
Collector to base voltage	VCBO	-100	V
Collector to emitter voltage	VCEO	-60	V
Emitter to base voltage	VEBO	-5	V
Collector current	IC	-2	A
Collector peak current	IC(peak)	-3	A
Collector power dissipation	PC*	20	W
Junction temperature	Tj	150	°C
Storage temperature	Tsig	-55 to +150	°C

* Value at Tc=25°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V(BR)CBO	IC = -1mA, IE = 0	-100	—	—	V
Collector to emitter breakdown voltage	V(BR)CEO	IC = -10mA, RE = ∞	-60	—	—	V
Emitter to base breakdown voltage	V(BR)EBO	IE = -1mA, IC = 0	-5	—	—	V
Collector cutoff current	ICBO	VCE = -80V, IE = 0	—	—	-1.0	μA
Emitter cutoff current	IEBO	VEB = -5V, IC = 0	—	—	-1.0	μA
DC current transfer ratio	hFE1*	VCE = -5V, IC = -0.5A**	60	—	200	
	hFE2	VCE = -5V, IC = -2A**	40	—	—	
Base to emitter voltage	VBE	VCE = -5V, IC = -1.5A**	—	—	-1.4	V
Collector to emitter saturation voltage	VCE(sat)	IC = -1.5A, IB = -0.15A**	—	-0.6	-1.0	V
Gain bandwidth product	fT	VCE = -5V, IC = -0.5A**	—	250	—	MHz
Collector output capacitance	Cob	VCE = -10V, IE = 0, f = 1MHz	—	50	—	pF

* The 2SB874 is grouped by hFE as follows.

** Pulse Test

B	C
60 to 120	100 to 200

